EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L8	0	003/030247.A2	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/26 11:21
L9	0	003/030247$2A2	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/26 11:21
L10	0	W003/030247$2A2	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/26 11:21

L11	0	W003/030247	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/26 11:21
L12	0	W003030247	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/26 11:21
L13	0	"003030247"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/26 11:22
L19	15195	(compres$3 near3 air) with (spray$3 coat$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/26 14:31
L20	1241	(((deposit$3 "CVD") with sputtering with (spray$3 coat $3)) with (insulator dielectric)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/26 14:32

L21	0	20 same 19	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/26 14:33
L22	1	20 and 19	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/26 14:33
L23	15749	(compres$4 near3 air) with (spray$3 coat$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/26 14:33
L24	1	20 and 23	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/26 14:35
L25	328	(compres$3 near3 air) near6 (insulator dielectric photo$2resist resist)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/26 14:37

L26	6	25 same (wafer substrate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/26 14:38
S1	11	("20020063332" | "20030052414" | "20050151249" | "3945030" | "4718977" | "5034346" | "5291066" | "5637922" | "6294741" | "6420209" | "6426242").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/13 12:58
S2	6	("3496426" | "3586549" | "3755001" | "3798514").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/08/13 13:56
S3	2	("3496426").URPN.	USPAT	OR	ON	2009/08/13 14:04
S4	9	("3388000" | "3405329" | "3491273" | "3496426" | "3604990").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/08/13 14:05
S5	8	("3945030").URPN.	USPAT	OR	ON	2009/08/13 14:08
S6	11	("3785862" | "3892606" | "3906540" | "3945030" | "4062033" | "4085498" | "4086613" | "4119992" | "4282647" | "4297149" | "4322453").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/08/13 14:09

S7	29	("4349408").URPN.	USPAT	OR	ON	2009/08/13 14:16
S8	8	("3945030").URPN.	USPAT	OR	ON	2009/08/13 14:23
S9	3868	(257/778).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	OFF	2009/08/14 11:01
S10	2653	(257/738).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	OFF	2009/08/14 11:01
S11	528	(257/789).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	OFF	2009/08/14 11:01
S12	742	(257/790).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	OFF	2009/08/14 11:01
S13	2	("3496426").URPN.	USPAT	OR	ON	2009/08/14 15:04

S14	13	("3834793" | "4058430" | "4755866" | "4783695" | "4907062" | "4918811" | "4930042" | "4937203" | "4960613" | "4988412" | "5002818" | "5108825" | "5127998").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/08/14 15:34
S15	1	("20080001244").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	OFF	2009/08/19 19:01
S16	93	(in$2organic near2 oxide) with photoresist	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/21 18:11
S17	48	(compres$3 near3 air) with photoresist	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/21 18:12
S18	3	(compres$3 near3 air) near4 photoresist	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/21 18:12

S19	6	(compres$3 near3 air) near6 photoresist	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/21 18:13
S20	0	S19 and S16	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/21 18:13
S21	0	S17 and S16	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/21 18:13
S22	48	(compres$3 near3 (air "H. sub.2O")) with photoresist	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/21 18:14
S23	0	S22 and S16	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/21 18:15

S24	652	((in$2organic near3 oxide) (dielectric near5 polymer)) with photoresist	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/21 18:36
S25	0	(compres$3 near3 (air "H. sub.2O")) same S24	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/21 18:37
S26	0	(compres$3 near3 (air "H. sub.2O")) and S24	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/21 18:37
S27	28	((in$2organic near3 oxide) (dielectric near5 polymer)) same (compres$3 near3 (air "H.sub.2O"))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/21 18:38
S28	6	((in$2organic near3 oxide) (dielectric near5 polymer)) with (compres$3 near3 (air "H.sub.2O"))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/21 18:38

S29	42	(in$2organic near2 oxide) near5 photoresist	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/21 18:46
S30	0	S29 same metalization	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/21 18:46
S31	238962	("438").CLAS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	OFF	2009/08/21 18:47
S32	20	S29 and S31	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/21 18:47
S33	439	(compres$3 near3 (gas$3 air)) same ((inorganic near3 oxide) (silicon near2 oxide) "SiO.sub.2" (titanium near2 oxide) "TiO.sub.2")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/22 10:59

S34	81	(compres$3 near3 (gas$3 air)) with ((inorganic near3 oxide) (silicon near2 oxide) "SiO.sub.2" (titanium near2 oxide) "TiO.sub.2")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/22 11:00
S35	238962	("438").CLAS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	OFF	2009/08/22 11:01
S36	462008	("257").CLAS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	OFF	2009/08/22 11:01
S37	1	S34 and (S35 S36)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/22 11:02
S38	1	S34 and (S35 S36)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/22 11:04

S39	184	(compres$3 near3 (gas$3 air)) with ((inorganic near3 oxide) (silicon near2 oxide) "SiO.sub.2" (titanium near2 oxide) "TiO.sub.2" insulat$3 dielectric) with spray$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/22 11:09
S40	22	(compres$3 near3 (gas$3 air)) near5 ((inorganic near3 oxide) (silicon near2 oxide) "SiO.sub.2" (titanium near2 oxide) "TiO.sub.2" insulat$3 dielectric) near5 spray$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/22 11:12
S41	14816610	@ad<"20040226" @rlad<"20040226"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/22 11:15
S42	19	S40 and S41	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/22 11:16
S43	147	S39 and S41	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/22 12:32

S44	3	S40 not S42	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/22 12:32
S45	0	S43 and (S35 S36)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/22 12:39
S46	0	S43 and transistor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/22 12:40
S47	1	S43 and diode	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/22 12:41
S48	19	S39 same (wafer substrate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/22 12:42

S49	18	S48 and S41	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/22 12:43
S50	110	S43 not (S42 S48)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/22 12:53
S51	5	(compres$3 near3 (gas$3 air)) same (((inorganic near3 oxide) (silicon near2 oxide) "SiO.sub.2" (titanium near2 oxide) "TiO.sub.2") with (photo$2resist resist))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/24 07:44
S52	14816610	@ad<"20040226" @rlad<"20040226"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/24 07:45
S53	2	S51 and S52	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/24 07:45

S54	184	(compres$3 near3 (gas$3 air)) with ((inorganic near3 oxide) (silicon near2 oxide) "SiO.sub.2" (titanium near2 oxide) "TiO.sub.2" insulat$3 dielectric) with spray$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/24 07:48
S55	15	(compres$3 near3 (gas$3 air)) with (photo$2resist resist) with spray$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/24 07:49
S56	96641	((((inorganic near3 oxide) (silicon near2 oxide) "SiO. sub.2" (titanium near2 oxide) "TiO.sub.2" insulat$3 dielectric) with (photo $2resist resist))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/24 07:50
S57	2	S55 and S56	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/24 07:51
S58	1	S54 and S56	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/24 07:55

S59	67874	(((inorganic near3 oxide) (silicon near2 oxide) "SiO. sub.2" (titanium near2 oxide) "TiO.sub.2" insulat$3 dielectric) with (photo $2resist photo$2sensitive))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/24 07:57
S60	0	S54 and S59	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/24 07:57
S61	0	S54 and S55	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/24 07:58
S62	165	(compres$3 near3 air) with ((in$2organic near3 oxide) (silicon near2 oxide) "SiO. sub.2" (titanium near2 oxide) "TiO.sub.2" insulat$3 dielectric) with spray$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/24 08:00
S63	16	(compres$3 near3 air) near5 ((in$2organic near3 oxide) (silicon near2 oxide) "SiO.sub.2" (titanium near2 oxide) "TiO.sub.2" insulat$3 dielectric) near5 spray$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/24 08:00

S64	13	S63 and S52	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/24 08:01
S65	238962	("438").CLAS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	OFF	2009/08/24 10:04
S66	462008	("257").CLAS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	OFF	2009/08/24 10:04
S67	535752	(S65 S66)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/24 10:04
S68	0	S67 and S62	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/24 10:05

S69	4038	(compres$3 near3 (gas$3 air)) with (insulat$3 dielectric)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/24 11:30
S70	35	S67 and S69	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/24 11:30
S71	2920	spray$3 with (dielectric insulator) with (coat$3 deposit$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/25 16:15
S72	2110824	substrate wafer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/25 16:16
S73	927	S71 same S72	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/25 16:16

S74	516	S71 with S72	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/25 16:16
S75	619914	S72 near4 (semiconductor silicon)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/25 16:17
S76	31	S71 with S75	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/25 16:17
S77	13025	spray$3 with (compres$4 near3 air)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/25 16:18
S78	0	S76 and S77	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/25 16:18

S79	0	S76 and (compres$4 near3 air)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/25 16:18
S80	52	S71 and S77	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/25 16:19
S81	4	S74 and S77	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/25 16:19
S82	0	S81 and S75	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/08/25 16:20
S83	31	("3984591").URPN.	USPAT	OR	ON	2009/08/25 16:22
S84	11	("3107177" | "3519467" | "3652246" | "3705054" | "3711322" | "3754975" | "3850665").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/08/25 16:31

EAST Search History (Interference)

\<This search history is empty\>

8/26/09 3:18:51 PM

C:\Documents and Settings\rpompey\My Documents\EAST\Workspaces\10590901_angled lead.wsp